OPB822S, OPB822SD OPB826S, OPB826SD

Features:

- Non-contact switching
- Single or double apertures for high resolution
- Choice of slot widths
- Choice of side-by-side or over/under dual channels
- Choice of electrical outputs



Description:

Each **OPB822** and **OPB826** slotted switch consists of two infrared emitting diodes and two NPN silicon phototransistors mounted on opposite sides of a 0.090" (2.29 mm) wide slot **(OPB822)** or a 0.100" (2.54 mm) wide slot **(OPB826)**.

OPB822 uses an side-by-side mounting configuration, while **OPB826** uses an over/under mounting configuration. **OPB822S** has 0.01" by 0.04" (0.25 mm x 1.02 mm) apertures in front of both phototransistors while the **OPB822SD** has the aperture in front of both phototransistors and both emitters. The **OPB826S** has 0.04" by 0.04" (1.02 mm x 1.02 mm) apertures in front of both phototransistors while the **OPB826SD** has the aperture in front of both phototransistors and both emitters.

Dual channels enable direction of travel sensing, with the low-cost plastic housing reduces possible interference from ambient light and provides protection from dust and dirt.

Phototransistor switching occurs when an opaque object passes through the device slot.

For information on encoder design, see Application Bulletin 203 at:

Custom electrical, wire and cabling and connectors are available. Contact your local

representative or OPTEK for more information.

Applications:

- Encoders
- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter/ Sensor	Lead Length / Spacing	
OPB822S Dual Dual 935 nm Transistor		0.09" / 0.30"	None / 0.01" 0.01" /	0.35" / 0.30"		
OPB822SD				0.01"		
OPB826S	65DualDual55D890 nmTransistor		0 10" /	NA / 0.04"	0.20" / 0.74"	
OPB826SD			0.42"	0.04" / 0.04"		



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPB822S, OPB822SD

OPB826S, OPB826SD



OPB822



Bottom View

Pin #	Description	Pin #	Description
8	Cathode-1	1	Collector-1
7	Anode-1	2	Emitter-1
6	Cathode-2	3	Collector-2
5	Anode-2	4	Emitter-2

Bottom View



Pin #	Description	Pin #	Description
8	Cathode-1	1	Collector-1
7	Cathode-2	2	Collector-2
6	Anode-2	3	Emitter-2
5	Anode-1	4	Emitter-1





OPB826



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OPB822S, OPB822SD



OPB826S, OPB826SD

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +85° C			
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] $^{(1)}$	240°C			
Input Diode				
Forward DC Current OPB822S, OPB822SD OPB826S, OPB826SD	50 mA 40 mA			
Peak Forward Current (1 μs pulse width, 300 pps)	1 A			
Reverse DC Voltage	2 V			
Power Dissipation ⁽²⁾	100 mW			

Output Phototransistor

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Collector DC Current	30 mA
Power Dissipation ⁽²⁾	100 mW

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25° C.
- (3) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones. Spray and wipe; do not submerge.
- (4) Derate linearly 3.33 mW/°C above 25° C.
- (5) All parameters tested using pulse techniques.
- (6) Feature controlled at body.

Encoder Sequence for OPB826









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OPB822S, OPB822SD



OPB826S, OPB826SD

Electrical Characteristics (OPB822, OPB826) (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	ΜΑΧ	UNITS	TEST CONDITIONS
Input Diode (see OP14O for OPB822 or OP266 for OPB826 for additional information)						
V _F	Forward Voltage	-	-	1.7	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V
Output Phototransistor (see OP550 for OPB822 or OP506 for OPB826 for additional information)						
V _{(BR)(CEO)}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _c = 1 mA
V _{(BR)(ECO)}	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _E = 100 μΑ
I _{CEO}	Collector-Emitter Leakage Current	-	-	100	nA	$V_{CE} = 10 V, I_F = 0, E_E = 0$
Coupled						
I _{C(ON)}	On-State Collector Current OPB822S OPB822SD OPB826S OPB826SD	250 100 250 100	- - -	- - -	μΑ μΑ μΑ	$V_{CE} = 5 V, I_F = 20 mA$ $V_{CE} = 5 V, I_F = 20 mA$ $V_{CE} = 10 V, I_F = 20 mA$ $V_{CE} = 10 V, I_F = 20 mA$
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OPB822S OPB822SD OPB826S OPB826SD		- - -	0.4 0.4 0.4 0.4	V V V V	$I_{c} = 125 \ \mu\text{A}, I_{F} = 20 \ \text{mA}$ $I_{c} = 50 \ \mu\text{A}, I_{F} = 20 \ \text{mA}$ $I_{c} = 125 \ \mu\text{A}, I_{F} = 20 \ \text{mA}$ $I_{c} = 50 \ \mu\text{A}, I_{F} = 20 \ \text{mA}$
I _{CX1}	Crosstalk OPB822D, OPB822SD OPB826S OPB826SD	- -	- - -	250 20 10	μΑ	I _{F1} = 0 mA, I _{F2} = 20 mA, V _{CE} = 10 V

Notes:

(1) All parameters tested using pulse techniques.

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